

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : **2001-318465**

(43)Date of publication of application : **16.11.2001**

---

(51)Int.Cl. G03F 7/039  
C08F220/00  
C08F222/04  
C08F232/08  
C08K 5/00  
C08L 33/04  
C08L 35/00  
C08L 45/00  
G03F 7/004  
H01L 21/027

---

(21)Application number : **2000-138882** (71)Applicant : **FUJI PHOTO FILM CO LTD**

(22)Date of filing : **11.05.2000** (72)Inventor : **SATO KENICHIRO**  
**AOSO TOSHIKI**

---

### (54) POSITIVE TYPE PHOTORESIST COMPOSITION

#### (57)Abstract:

PROBLEM TO BE SOLVED: To provide a positive type resist composition having good PED, sensitivity and resolving power in the formation of contact holes in relation to lithography using a short-wavelength exposure light source for ultra-microfabrication and a positive type chemical amplification resist.

SOLUTION: The positive type resist composition contains (A) a resin containing repeating structural units each having a specified acid decomposable group and having the velocity of dissolution in an alkali developing solution increased by the action of an acid and (B) a compound which generates the acid when irradiated with active light or radiation.

---

### LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's  
decision of rejection]

[Date of requesting appeal against  
examiner's decision of rejection]

[Date of extinction of right]